## **DIODE MODULE**

## **DD110F/KD110F**







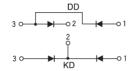
UL;E76102 (M)

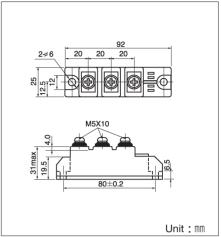
Power Diode Module **DD110F** series are designed for various rectifier circuits. **DD110F** has two diode chips connected in series in 25mm (1inch) width package and the mounting base is electrically isolated from elements for simple heatsink construction. Wide voltage rating up to, 1,600V is avaiable for various input voltage.

- Isolated mounting base
- Two elements in a package for simple (single and three phase) bridge connections
- Highly reliable glass passivated chips
- High surge current capability

(Applications)

Various rectifiers, Battery chargers, DC motor drives





■Maximum Ratings (Tj=25°C)

Symbol	Itam	Ratings				Limit
	Item	DD110F40	DD110F80	DD110F120	DD110F160	Unit
VRRM	Repetitive Peak Reverse Voltage	400	800	1200	1600	V
VRSM	Non-Repetitive Peak Reverse Voltage	480	960	1300	1700	V

Symbol	Item		Conditions	Ratings	Unit
IF (AV)	Average Forward Current		Single phase, half wave, 180° conduction, Tc:88°C	110	Α
IF (RMS)	R.M.S. Forward Current		Single phase, half wave, 180° conduction, Tc: 88°C	172	Α
IFSM	Surge Forward Current		½ cycle, 50/60Hz, peak value, non-repetitive	2300/2550	Α
l²t	I²t		Value for one cycle of surge current	26500	A <sup>2</sup> S
Viso	Isolation Breakdown Voltage (R.M.S)		A.C.1minute	2500	V
Tj	Junction Temperature			<b>−</b> 40∼ <b>+</b> 125	°C
Tstg	Storage Temperature			<b>−</b> 40∼ <b>+</b> 125	°C
	Mounting	Mounting (M5)	Recommended Value 1.5~2.5 (15~25)	2.7 (28)	N·m
	Torque	Terminal (M5)	Recommended Value 1.5~2.5 (15~25)	2.7 (28)	(kgf·cm)
	Mass			170	g

## **■**Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
IRRM	Repetitive Peak Reverse Current, max.	at VDRM, single phase, half wave. Tj=125℃	20	mA
VFM	Forward Voltage Drop, max.	Forward current 350A, Tj=25°C, Inst. measurement	1.45	V
Rth (j-c)	Thermal Impedance, max.	Junction to case	0.25	°C/W

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